

Roll No: Subject Code: KOE048

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BTECH (SEM IV) THEORY EXAMINATION 2021-22 ELECTRONICS ENGINEERING

Time: 3 Hours Total Marks: 100

Note: Attempt all Sections. If you require any missing data, then choose suitably.

SECTION A

Attem	apt all questions in brief. 2x10	= 20
Qno	Questions	CO
(a)	Si is preferred as compared to Ge in semiconductor devices. Justify this statement.	1
(b)	Describe the term PIV.	1
(c)	Enlist the application of LED.	2
(d)	Describe the tunneling phenomenon.	2
(e)	Derive the relationship between α and β for BJT.	3
(f)	Draw the transfer characteristics of JFET.	3
(g)	Describe the term CMRR and slew rate of an op-amp.	4
(h)	Enlist the characteristics of ideal op-amp.	4
(i)	Enlist the essential components of a CRT.	5
(j)	Explain the application of DSO.	5

SECTION B

2.	Attempt any <i>three</i> of the following:	C	-	(0	10x3	= 30
		2		1			

Qno	Questions	CO
(a)	Explain the working of PN junction diode with no-bias condition, forward	1 •
	bias condition and reverse bias condition. Also draw the V-I characteristics of	6,
	PN junction diode.	•
(b)	Illustrate the working of half wave rectifier using circuit diagram also	2
	determine its different parameter.	
(c)	Mention the different biasing techniques used in BJT. Explain any two of	3
	them.	
(d)	Draw the block diagram and equivalent circuit of an op-amp. Also explain op-	4
	amp as inverting and non-inverting amplifier.	
(e)	Illustrate the working of digital multimeter with their block diagram.	5

SECTION C

3. Attempt any *one* part of the following: 10x1 = 10

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Qno		Questions	*			CO
(a)	Illustrate the diode	resistance and diode capacitance	e.			1
(b)	Differentiate between mechanism.	veen Avalanche breakdown	and	Zener	Breakdown	1

4. Attempt any *one* part of the following:

Qno					Questions	CO
(a)	Determine	e the ou	tput vo	oltage and c	utput waveform for a given input	2
	waveform	. Assun	ning S	ilicon diode	s.	
	+ vi	f = 100			$C = 1 \mu F$	
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(b)	Explain the principle of operation and characteristics of an LED and Tunnel	2
	diode.	

5. Attempt any <i>one</i> part of the following:
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10x1	=10
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Qno	Questions					
(a)	Draw the CE amplifier circuit and derive the expression for different	3				
	characterizing parameters.					
(b)	(i) Explain the construction and working of JFET.	3				
	(ii) An enhancement type NMOS transistor with Vt =0.7 V has its source					
	terminal grounded and a 1.5 V applied to the gate. In what region does the					
	device operate for					
	a) $V_D = 0.5 \text{ V}$ b) $V_D = 0.9 \text{ V}$ c) $V_D = 3 \text{ V}$.					

6. Attempt any *one* part of the following:

10	0x1	=	1	0

Qno	Questions	CO		
(a)	Draw the circuit diagram of an integrator and differentiator also find their	4		
	output.			
(b)	Illustrate the following op-amp parameters			
	(i) input offset voltage			
	(ii) output offset voltage			
	(iii) input biased current			
	(iv) input offset current	1.		
	(v) differential mode gain	0,		

7. Attempt any *one* part of the following:

Qno	Questions	CO
(a)	Describe measurement of voltage, current, frequency and phase using CRO.	5
(b)	Draw the block diagram of digital voltmeter. Also explain the ramp technique	5
	of digital multimeter.	
	04.08.2022 \(\alpha\frac{1}{2}\fr	